Product data sheet

1. General description

Ultrafast power diode in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- Fast switching
- Guaranteed ESD capability
- · High thermal cycling performance
- Low on-state loss
- Low thermal resistance
- · Rugged: reverse voltage surge capability
- Soft recovery minimizes power-consuming oscillations

3. Applications

· Output rectifiers in high-frequency switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter Conditions		Values				Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			100			V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 128 °C; square-wave pulse; Fig. 1; Fig. 2		8			А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 128 °C; square-wave pulse	16			Α	
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	80			А	
	forward current	t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	88			Α	
Symbol	Parameter	Conditions	Min Typ Max		Max	Unit	
Static ch	aracteristics						
V _F	forward voltage	I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>		-	8.0	0.895	V
Dynamic	characteristics				'		
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; ramp recovery; Fig. 5; Fig. 7$		-	20	25	ns
Electrost	atic discharge						
V_{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ		-	-	8	kV

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	
2	А	anode]	K — A 001aaa020
mb	mb	mounting base; cathode	1 2 TO-220AC (SOD59)	001aaa020

6. Ordering information

Table 3. Ordering information

Type number Package					
	Name	Description	Version		
BYW29E-100 TO-220		plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59		

7. Marking

Table 4. Marking codes

Type number	Marking codes
BYW29E-100	BYW29E-100

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		100	V
V_{RWM}	crest working reverse voltage		100	V
V_R	reverse voltage		100	V
$I_{F(AV)}$	average forward current	δ = 0.5 ; $T_{mb} \le$ 128 °C ;square-wave pulse; Fig. 1; Fig. 2	8	А
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_{mb} \le 128 °C$; square-wave pulse	16	А
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	80	А
	forward current	t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	88	А
I _{RRM}	repetitive peak reverse current	$\delta = 0.001 \; ; t_p = 2 \; \mu s$	0.2	А
I _{RSM}	non-repetitive peak reverse current	t _p = 100 μs	0.2	А
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		150	°C
Electrosta	atic discharge		1	
V _{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ	8	kV

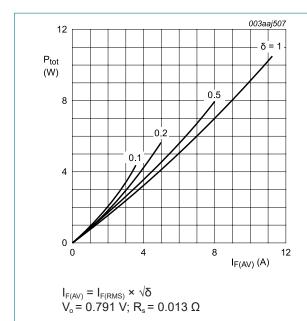
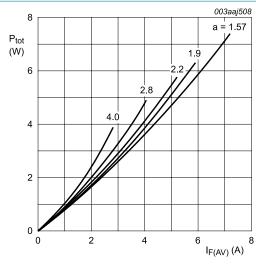


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 0.791 V; R_s = 0.013 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	Fig. 3	-	-	2.7	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

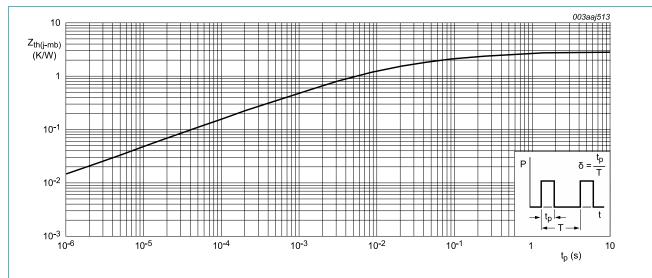
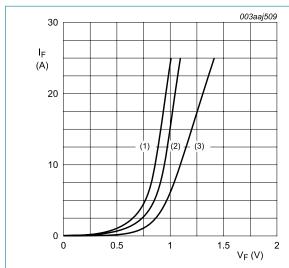


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse width

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 4</u>		0.92	1.05	V
		I _F = 20 A; T _j = 25 °C; <u>Fig. 4</u>	-	1.1	1.3	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>	-	0.8	0.895	V
I _R	reverse current	V _R = 100 V; T _j = 25 °C	-	2	10	μA
		V _R = 100 V; T _j = 100 °C	-	0.2	0.6	mA
Dynamic	characteristics					
Q _r	recovered charge	$I_F = 2 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 20 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 5; Fig. 6$	-	4	11	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A}/\mu\text{s}$; $T_j = 25 \text{ °C}$; ramp recovery; Fig. 5; Fig. 7	-	20	25	ns
		$I_F = 0.5 \text{ A}; I_R = 1 \text{ A}; I_{R(meas)} = 0.25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ step recovery}; Fig. 8$	-	15	20	ns
V _{FRM}	forward recovery voltage	I _F = 1 A; dI _F /dt = 10 A/μs; T _j = 25 °C; Fig. 9	-	1	-	V



(1) T_i = 150 °C; typical values

(2) T_i = 150 °C; maximum values

(3) $T_j = 25$ °C; maximum values

 $\dot{V}_{o} = 0.791 \text{ V}; R_{s} = 0.013 \Omega$



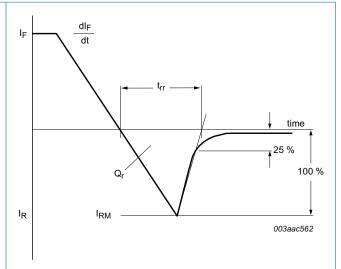
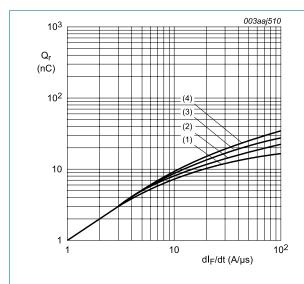


Fig. 5. Reverse recovery definitions; ramp recovery



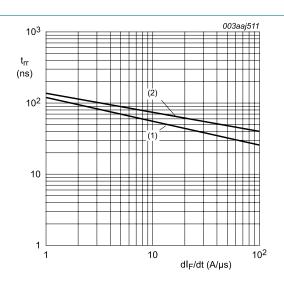
(1)
$$I_F = 1 A$$
; $T_j = 25 °C$

(2)
$$I_F = 2 A$$
; $T_i = 25 °C$

(3)
$$I_F = 5 A$$
; $T_j = 25 °C$

(4)
$$I_F = 10 \text{ A}$$
; $T_j = 25 \text{ °C}$

Fig. 6. Recovered charge as a function of rate of change of forward current; maximum values



(1)
$$I_F = 1 \text{ A}$$
; $T_j = 25 ^{\circ}\text{C}$
(2) $I_F = 10 \text{ A}$; $T_i = 25 ^{\circ}\text{C}$

Fig. 7. Reverse recovery time as a function of rate of change of forward current; maximum values

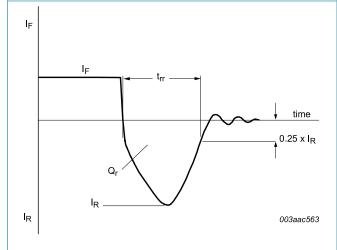


Fig. 8. Reverse recovery definitions; step recovery

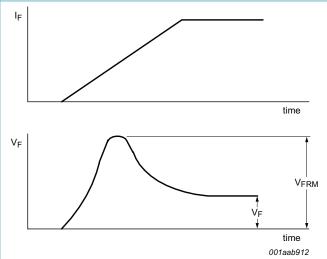
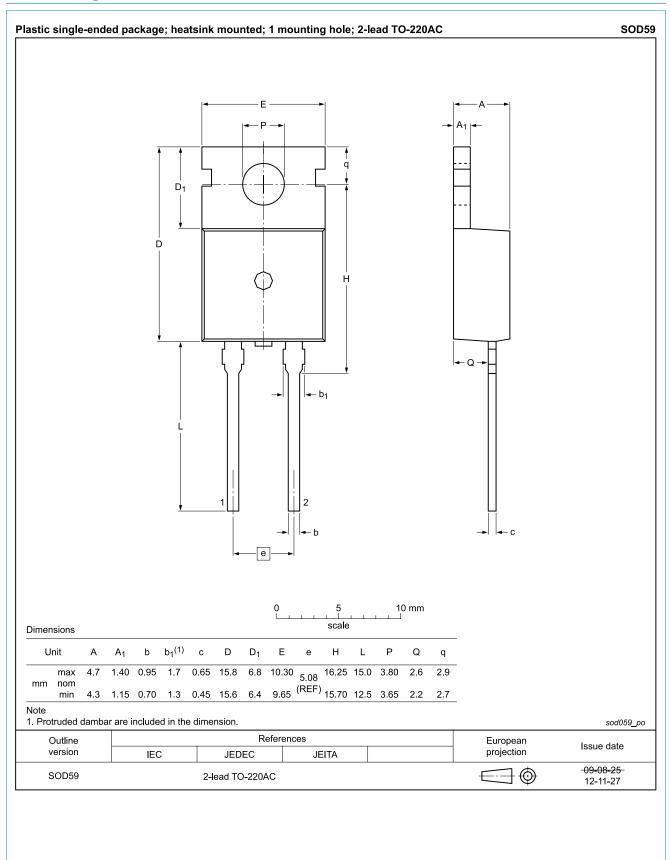


Fig. 9. Forward recovery definitions

11. Package outline



12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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